

IN THE CLAIMS:

The following is a complete listing of the claims in this application, reflects all changes currently being made to the claims, and replaces all earlier versions and all earlier listings of the claims:

1. (Currently Amended) A photoelectric converter comprising a photoelectric conversion element of a laminated structure comprising:
 - a first electrode layer;
 - an insulation layer for blocking the passage of holes and electrons;
 - a photoelectric conversion semiconductor layer;
 - an injection blocking layer for blocking the injection of only one of the holes or the electrons to said photoelectric conversion semiconductor layer;
 - a second electrode layer; [[and]]
 - a switching means for operating the photoelectric converter by switching through operation modes including a photoelectric conversion mode, an idling mode, and a refresh mode, wherein:
 - a) the photoelectric conversion mode emits one of the holes or the electrons, whichever one is emitted in the idling mode, generated in accordance with an amount of incident light and for reading image information,
 - b) the idling mode, not for reading the image information, emits one of the holes or the electrons, whichever one is emitted in the photoelectric conversion mode, from the photoelectric conversion element by connecting a switching element and an idle

terminal connected to a power source for applying an electric field weaker than an electric field applied in the photoelectric conversion mode, [[and]]

c) the refresh mode emits the other of the holes or the electrons from the photoelectric conversion element, and

d) a power source portion having at least a potential for the photoelectric conversion mode, a potential for the idling mode and a potential for the refresh mode and providing the photoelectric conversion element with an electric field, wherein the potential for the idling mode provides, in the idling mode, the photoelectric conversion element with an electric field which is in the same direction as the photoelectric conversion mode and which is weaker than an electric field applied in the photoelectric conversion mode.

2. (Previously Presented) The photoelectric converter according to claim 1, wherein a potential difference V_{dg} obtained by subtracting the potential of said second electrode layer from the potential of said first electrode layer of the photoelectric conversion element in the idling mode is smaller than a potential difference V_{dg} obtained by subtracting the potential of said second electrode layer from the potential of said first electrode layer of the photoelectric conversion element in the photoelectric conversion mode.

3. (Previously Presented) The photoelectric converter according to claim 1, wherein a recess mode of the photoelectric conversion element is provided for by applying a zero electric field to each layer before the idling mode.

4.-6. (Canceled)

7. (Previously Presented) The photoelectric converter according to claim 1, wherein:

a plurality of the photoelectric conversion elements are arranged one-dimensionally or two-dimensionally,

the switching element is connected for each of the photoelectric conversion elements,

all the photoelectric conversion elements are divided into a plurality of n blocks,

a light signal from the photoelectric conversion elements divided into n blocks is output with a matrix signal wiring by operating the switching element for each of the blocks, and

an intersection part of the matrix signal wiring comprises a lamination structure in which at least a first electrode layer, an insulating layer, a semiconductor layer and a second electrode layer are provided in this order, each corresponding to said first electrode layer, said insulating layer, said photoelectric conversion semiconductor layer, and said second electrode layer of the photoelectric conversion element.

8. (Currently Amended) A system comprising:

a photoelectric converter comprising a photoelectric conversion element of a laminated structure comprising:

a first electrode layer;

an insulation layer for blocking the passage of holes and electrons;

a photoelectric conversion semiconductor layer;

an injection blocking layer for blocking the injection of only one of the holes or the electrons to the photoelectric conversion semiconductor layer;

a second electrode layer; [[and]]

a switching means for operating the photoelectric converter by switching through operation modes including a photoelectric conversion mode, an idling mode, and a refresh mode, wherein:

a) the photoelectric conversion mode emits one of the holes or the electrons, whichever one is emitted in the idling mode, generated in accordance with an amount of incident light and for reading image information,

b) the idling mode, not for reading the image information, emits one of the holes or the electrons, whichever one is emitted in the photoelectric conversion mode, from the photoelectric conversion element by connecting the switching element and an idle terminal connected to a power source for applying an electric field weaker than an electric field applied at the photoelectric conversion mode, [[and]]

c) the refresh mode emits the other of the holes or the electrons from the photoelectric conversion element[[:]], and

d) a power source portion having at least a potential for the photoelectric conversion mode, a potential for the idling mode and a potential for the refresh mode and providing the photoelectric conversion element with an electric field, wherein the potential

for the idling mode provides, in the idling mode, the photoelectric conversion element with an electric field which is in the same direction as the photoelectric conversion mode and which is weaker than an electric field applied in the photoelectric conversion mode;

a signal processing means for processing a signal from the photoelectric converter;

a recording means for recording a signal from said signal processing means;

a display means for displaying a signal from said signal processing means;

an electric transmission means for electrically transmitting a signal from said signal processing means; and

a radiation source for generating radiation.

9. (Previously Presented) The photoelectric converter according to claim 2, wherein the potential V_{dg} is greater than zero.

10. (Previously Presented) The system according to claim 8, further comprising a phosphor for converting a wavelength of radiation.

11. (Previously Presented) The photoelectric converter according to Claim 1, wherein the switching element comprises a thin film transistor having the same layer construction as the photoelectric converter.